



### General Description

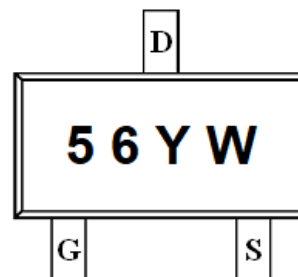
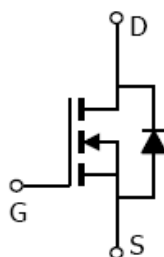
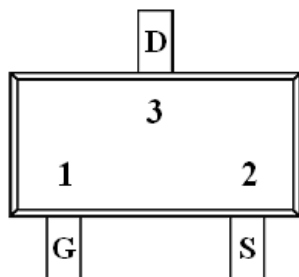
AFN2356AS, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- 100V/3.6A,  $R_{DS(ON)}=100m\Omega@V_{GS}=10V$
- 100V/2.8A,  $R_{DS(ON)}=125m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

### Pin Description ( SOT-23 )



### Application

- DC/DC Converters
- Load Switch
- LED Backlighting in LCD TVs

### Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN2356ASS23RG	56YW	SOT-23	Tape & Reel	3000 EA

- ※ 56 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFN2356ASS23RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



### Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

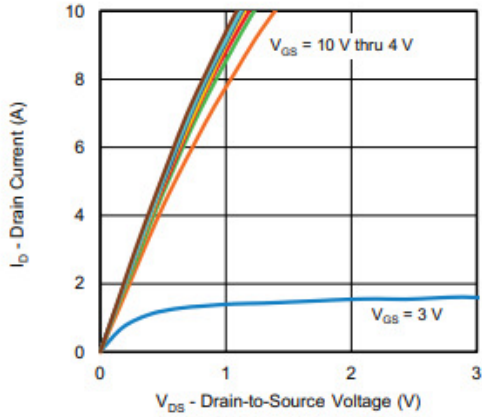
Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	3.6
		T <sub>A</sub> =70°C	2.8
Pulsed Drain Current	I <sub>DM</sub>	10	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	1.25
		T <sub>A</sub> =70°C	0.8
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

### Electrical Characteristics (T<sub>A</sub>=25°C Unless otherwise noted)

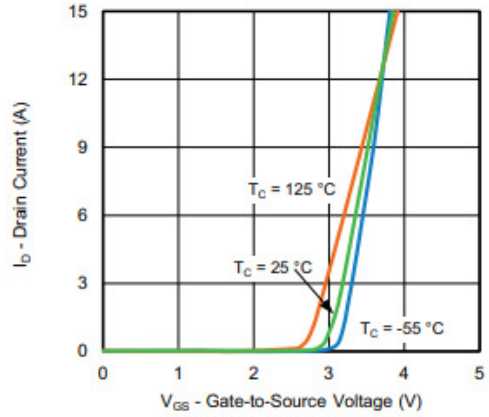
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0		2.5	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			10	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.6A		90	100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.8A		113	125	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3.6A		18		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V		0.8	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =4.5V I <sub>D</sub> ≅1.0A		2.7	5.4	nC
Gate-Source Charge	Q <sub>gs</sub>			1.3		
Gate-Drain Charge	Q <sub>gd</sub>			0.6		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V f=1MHz		345		pF
Output Capacitance	C <sub>oss</sub>			25		
Reverse Transfer Capacitance	C <sub>rss</sub>			5		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, R <sub>L</sub> =50Ω I <sub>D</sub> ≅1.0A, V <sub>GEN</sub> =10V R <sub>G</sub> =1Ω		10	20	ns
	t <sub>r</sub>			5	10	
Turn-Off Time	t <sub>d(off)</sub>			15	30	
	t <sub>f</sub>			5	10	



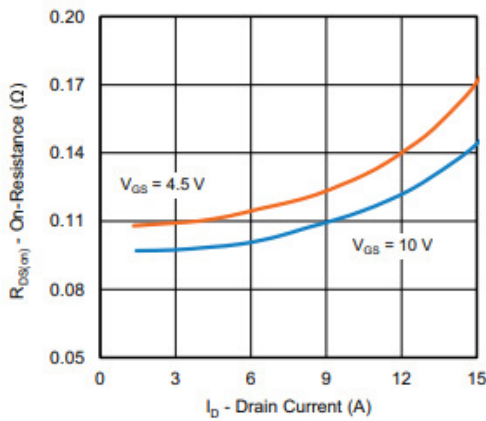
## Typical Characteristics



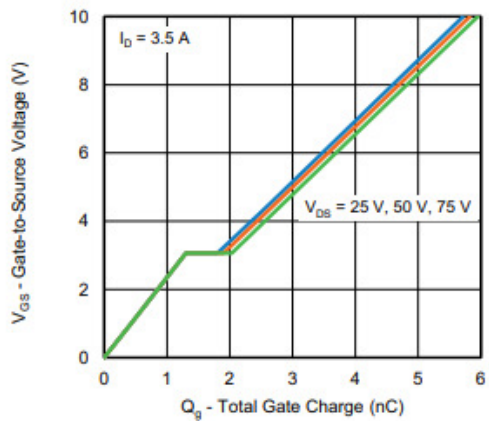
Output Characteristics



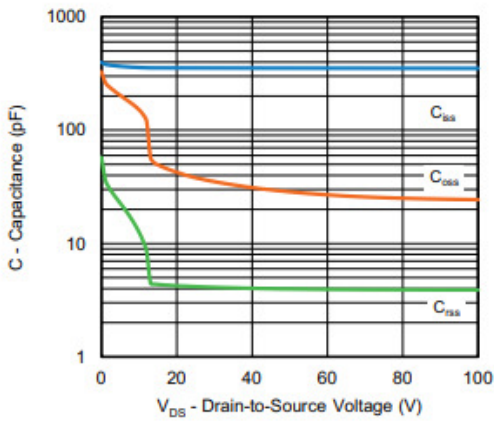
Transfer Characteristics



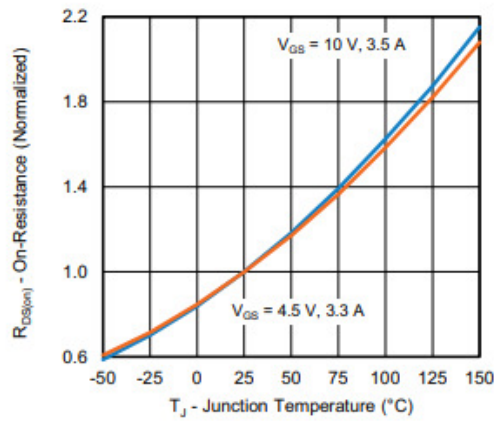
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



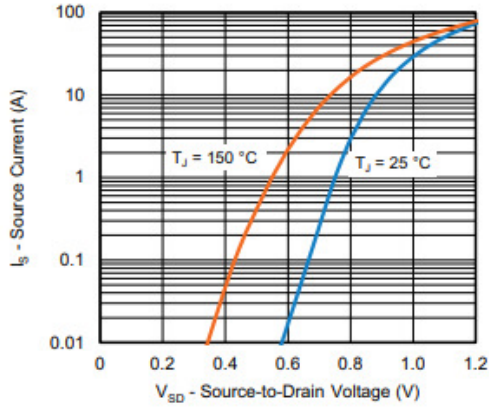
Gate Charge



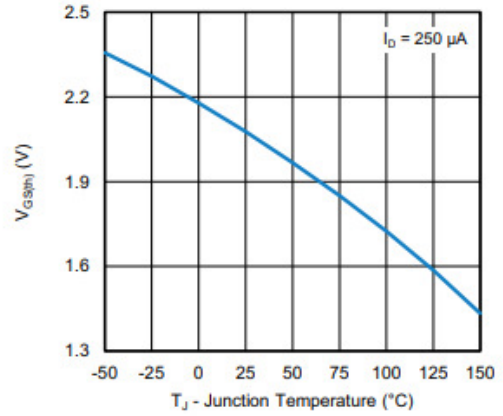
On-Resistance vs. Junction Temperature



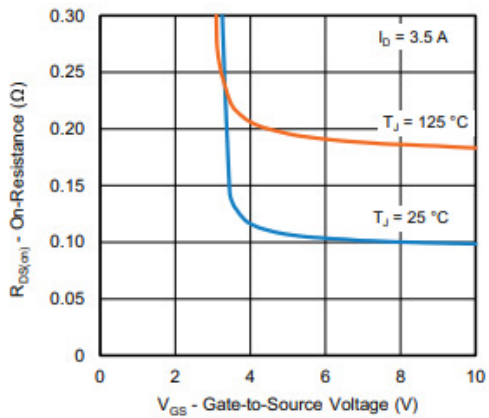
## Typical Characteristics



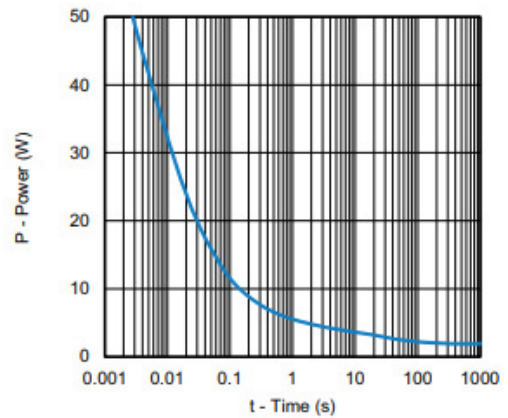
Source-Drain Diode Forward Voltage



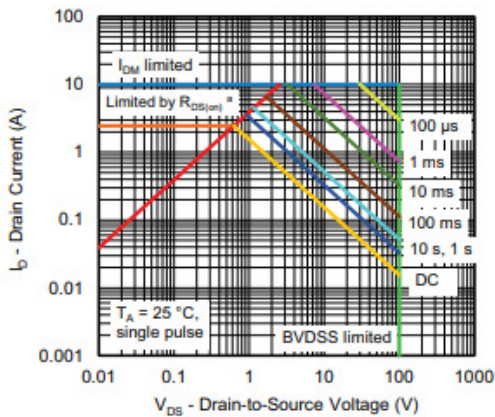
Threshold Voltage



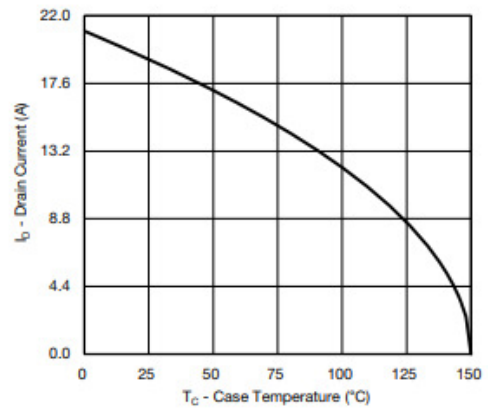
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



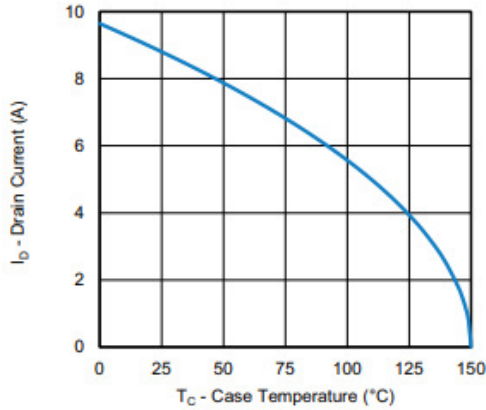
Safe Operating Area, Junction-to-Ambient



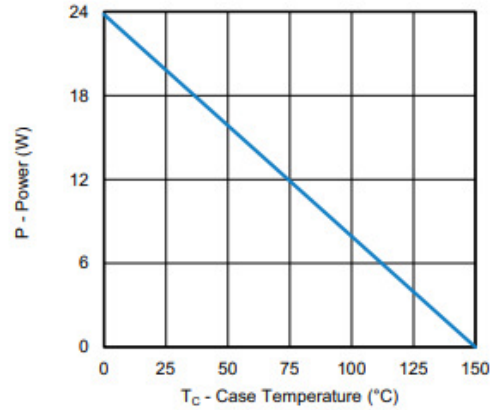
Current Derating\*



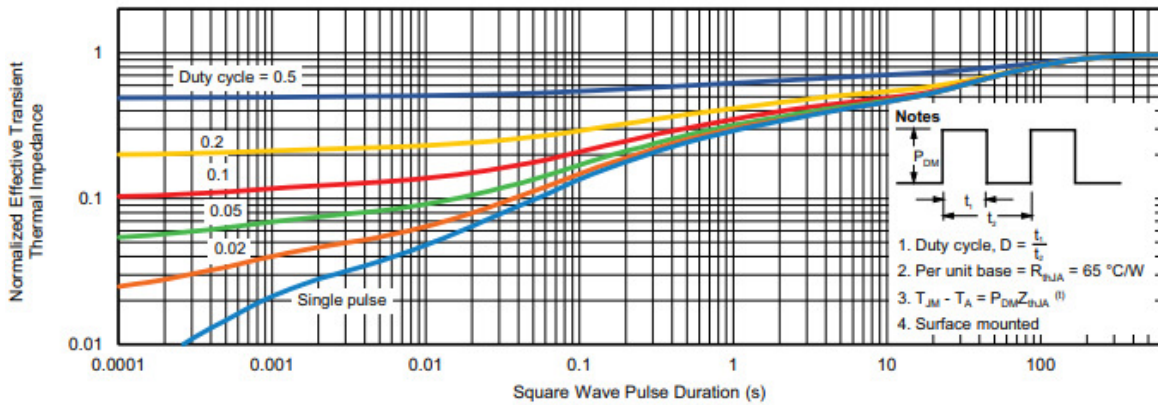
## Typical Characteristics



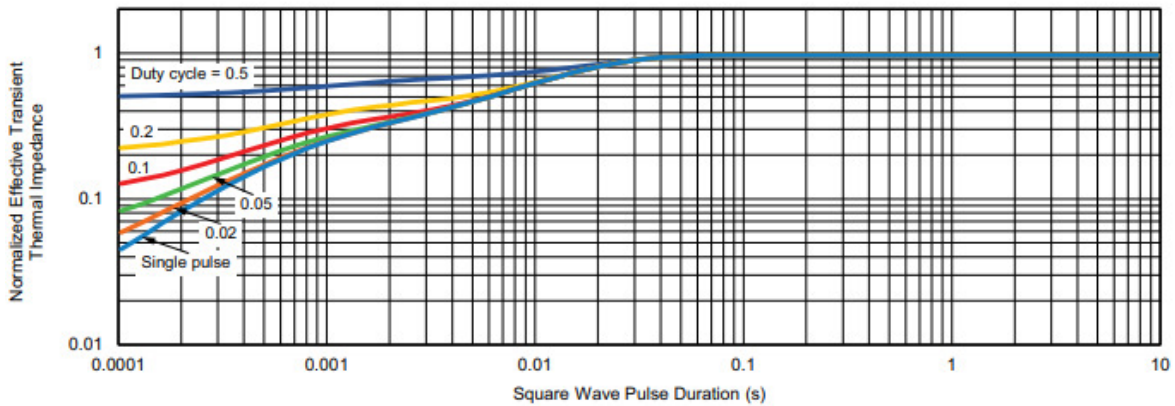
Current Derating <sup>a</sup>



Power, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

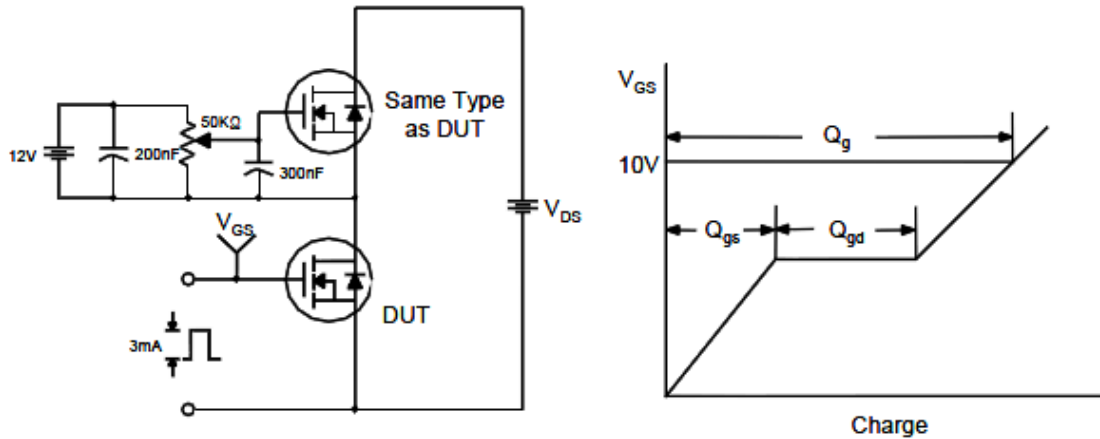


Normalized Thermal Transient Impedance, Junction-to-Case

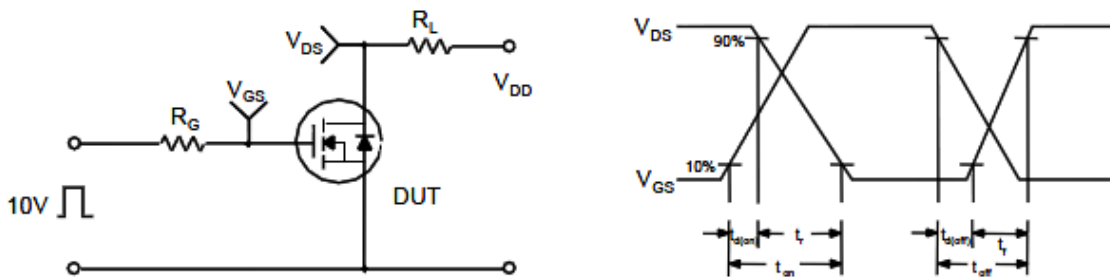


**Typical Characteristics**

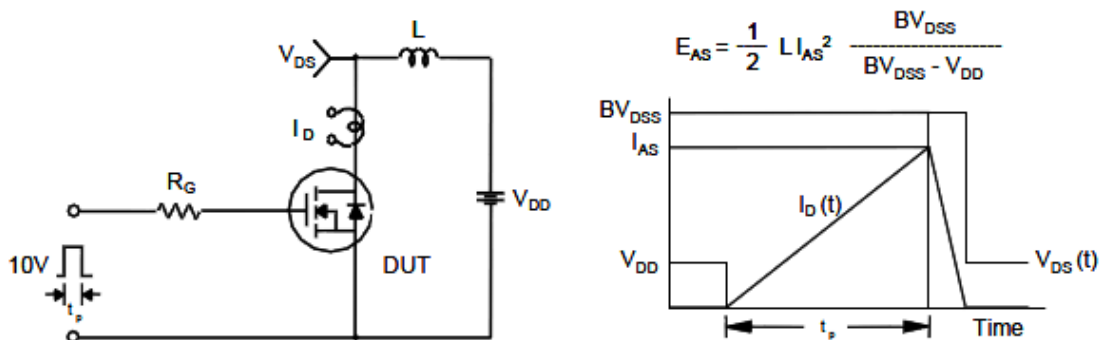
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



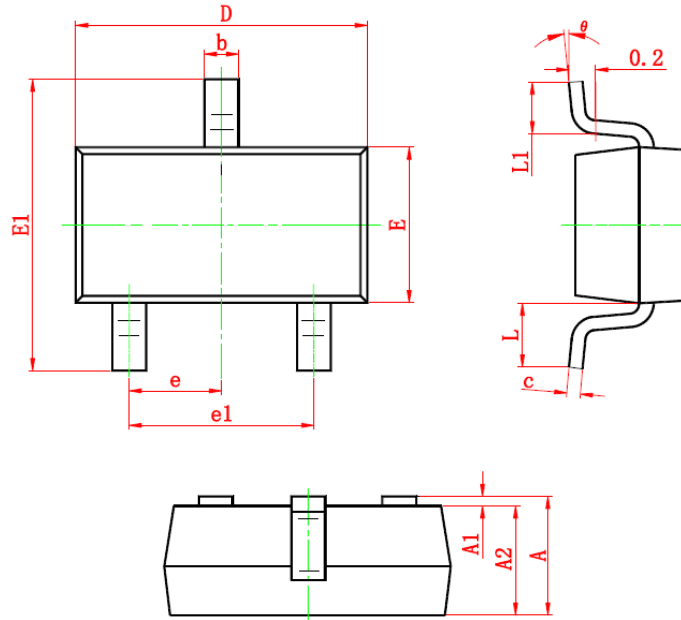
Unclamped Inductive Switching Test Circuit & Waveforms







**Package Information ( SOT-23 )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	6°

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